

IN THE SPECIFICATION

Please amend paragraph 15 as follows:

[0015] P-contact 9 and n-contact 10 of Fig. 1A may be multilayer structures, as illustrated in Figs. 1B and 1C. Fig. 1B illustrates an example of a multilayer p-contact 9. A layer of Au-Zn alloy 9A is formed adjacent to current spreading layer 3, in order to provide ohmic contact to the semiconductor layer. Au-Zn layer 9A may be protected by an optional guard metal layer 9B of, for example, a sandwich of TiW, TiW:N, and TiW. A thick contact layer 9C, such as gold, is then formed over guard layer 9B. The ohmic layer 9A and guard layer 9B may cover all or just a portion of the semiconductor layer 3 on which p-contact 9 is formed under reflector 9C.

Please amend paragraph 16 as follows:

[0016] A multilayer n-contact 10 may have a similar structure, as illustrated in Fig. 1C. A layer of Au-Ge alloy 10A is formed adjacent to contact layer 8, in order to provide ohmic contact to the semiconductor layer. Au-Ge layer 10A may be protected by an optional guard metal layer 10B of, for example, a sandwich of TiW, TiW:N, and TiW. A thick reflective layer 10C of Au is deposited over layers 10A and 10B. Ohmic layer 10A is generally not very reflective, and is thus often formed as dots (as in Fig. 1C) or thin stripes that cover a small fraction of the semiconductor layer 8 on which n-contact 10 is formed under reflector 10C.

Please amend paragraph 17 as follows:

[0017] Highly Heavily doped layers 4 (represented as thick dashed lines in Fig. 1A) may be included in one or more of p-doped contact layer 3, p-doped cladding layer 5, and n-doped cladding layer 7. Heavily doped layers 4 are formed in regions of the device that may benefit from additional current spreading. In the device illustrated in Fig. 1A, p-contact 9 does not directly overlie the active region, thus current is required to spread from p-contact 9 to the active region. Accordingly, the p-type side of active region 6 may benefit from additional current spreading and may thus include highly heavily doped layers 4. If n-contact 10 is a sheet contact, n-contact 10 overlies the entire active region and additional current spreading is not required on the n-type side of active region 6. If n-contact 10 includes small regions of ohmic layers 10A and a large reflective sheet 10C as illustrated in Fig. 1C, current

is required to spread from ohmic contact regions 10A to the areas of semiconductor layer 8 under reflective sheet 10C without an ohmic contact region 10A. In such devices, the n-type side of active region 6 may benefit from additional current spreading and may thus include highly heavily doped layers 4.

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